

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / PROFESSIONAL

PART NUMBER: RHRG50120

MANUFACTURER: INTERSIL

REMARK: TC=25C

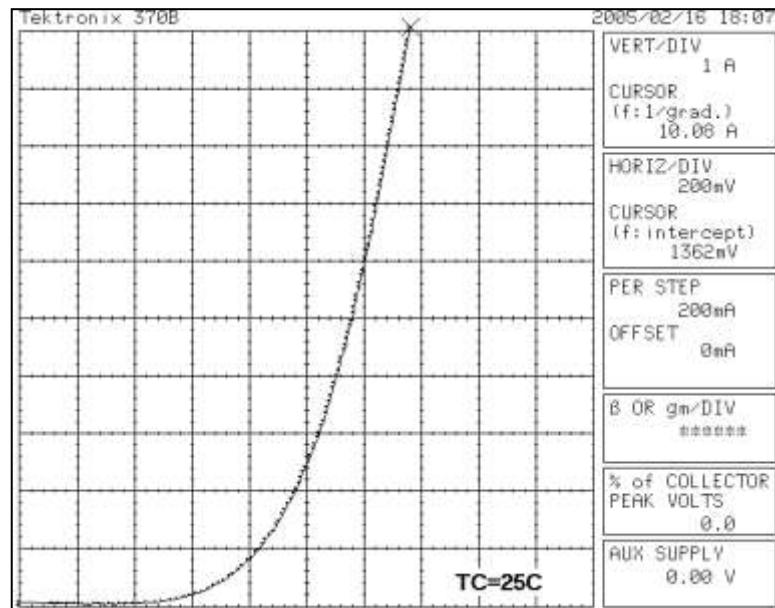


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

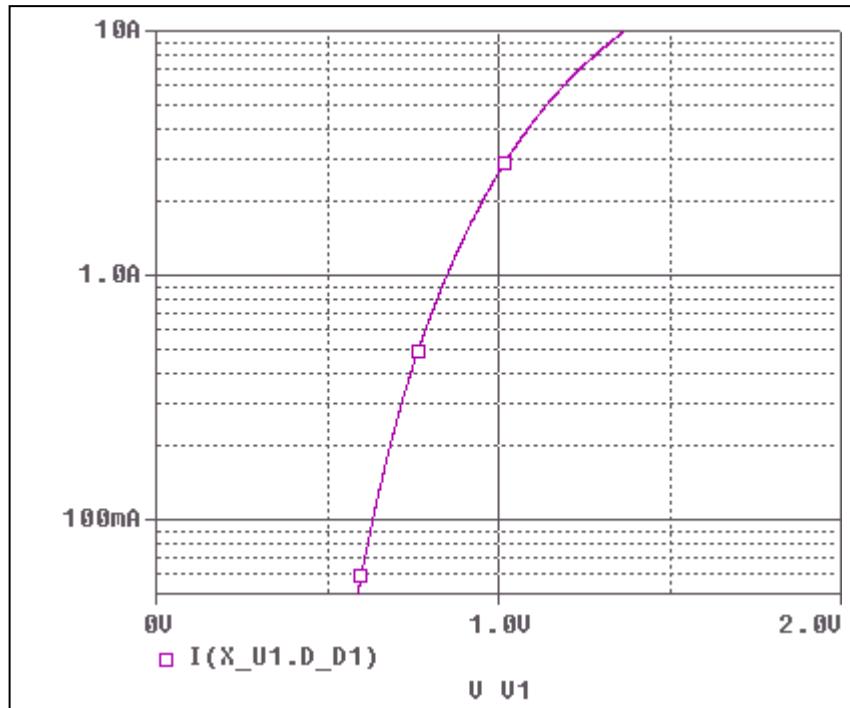
Forward Current Characteristic

Reference

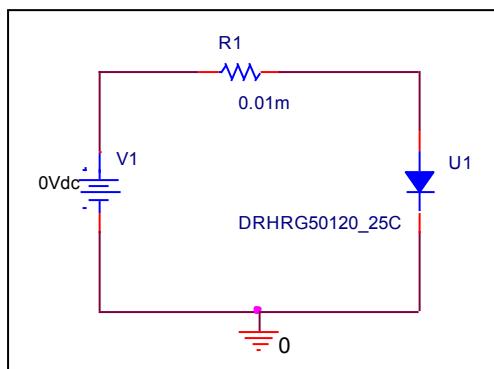


Forward Current Characteristic

Circuit Simulation Result

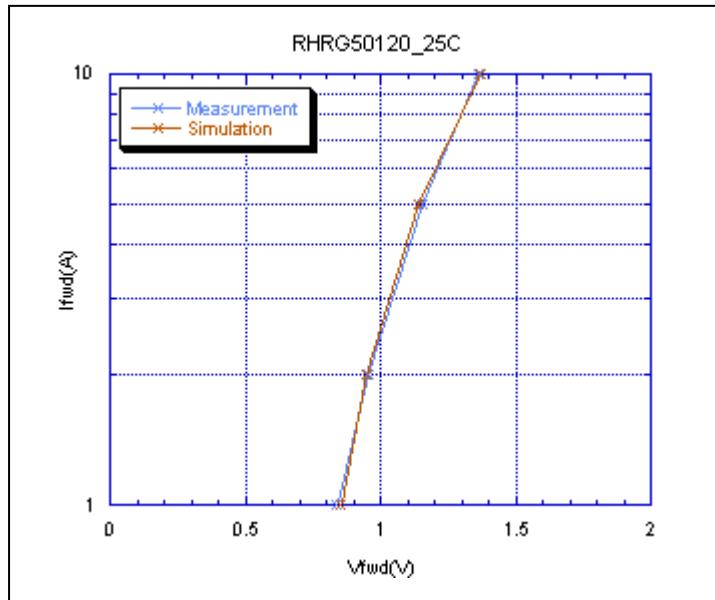


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

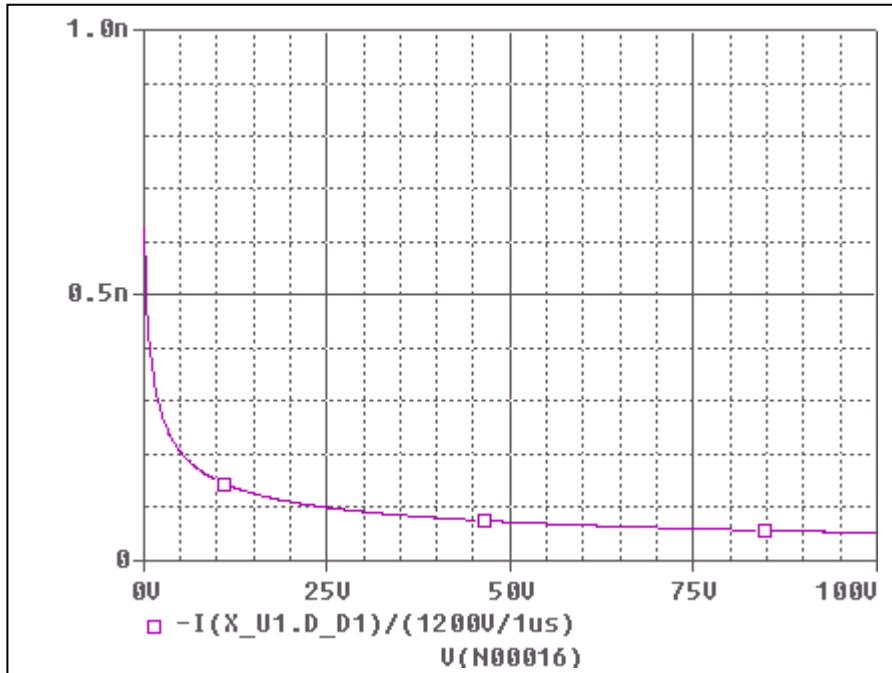


Simulation Result

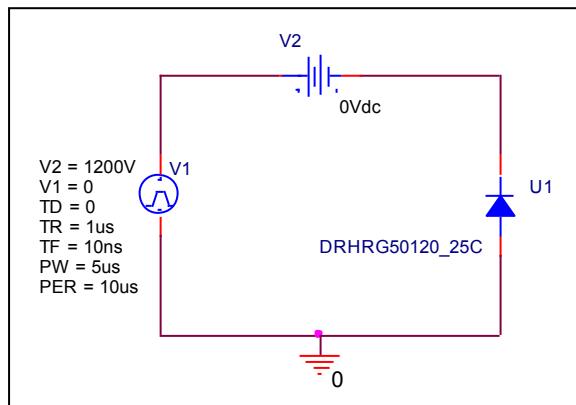
$I_{fwd}(A)$	$V_{fwd}(V)$ Measurement	$V_{fwd}(V)$ Simulation	%Error
1	0.834	0.849	-1.81
2	0.958	0.951	0.73
5	1.156	1.141	1.30
10	1.362	1.368	-0.44

Capacitance Characteristic

Circuit Simulation Result

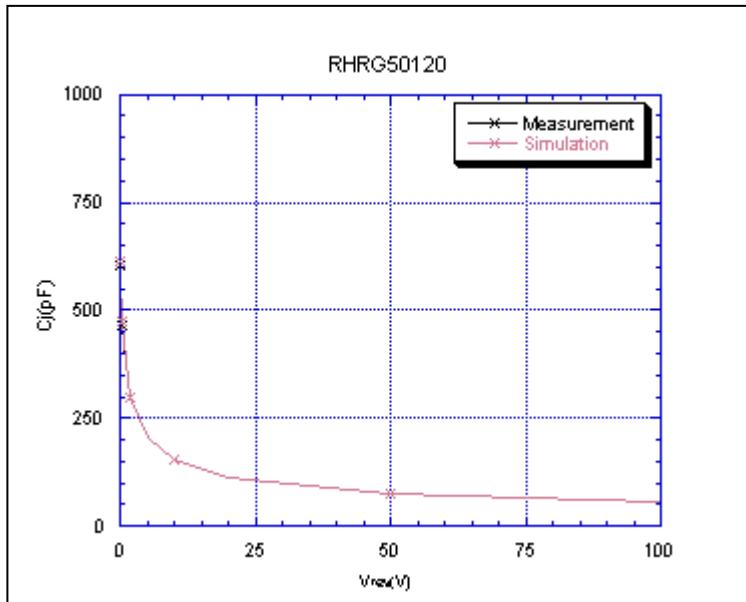


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

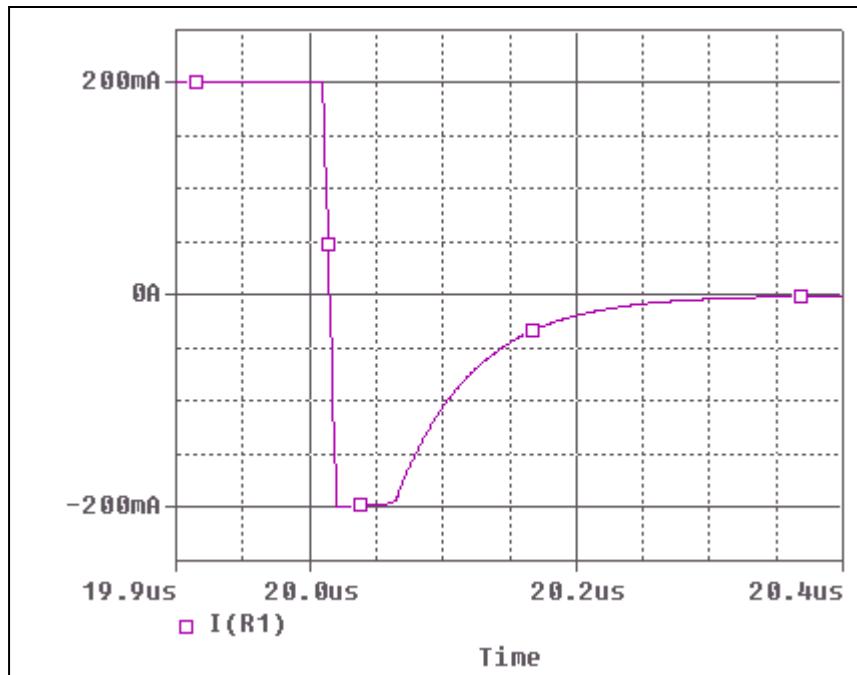


Simulation Result

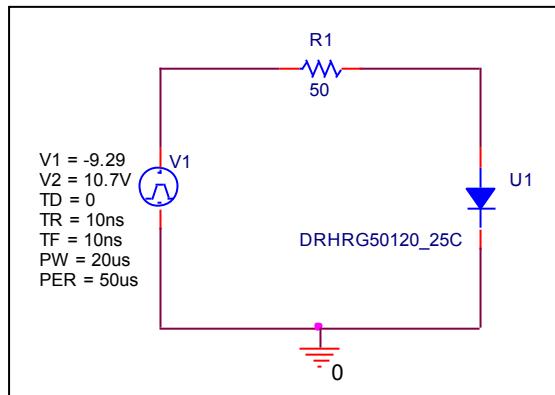
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	664.160	644.158	3.01
0.1	604.880	615.100	-1.69
0.2	560.900	579.121	-3.25
0.5	465.330	474.200	-1.91
1	382.770	383.222	-0.12
2	298.290	300.001	-0.57
5	205.900	206.101	-0.10
10	152.110	151.867	0.16
20	111.220	110.943	0.25
50	73.024	74.842	-2.49
100	53.020	52.873	0.28

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

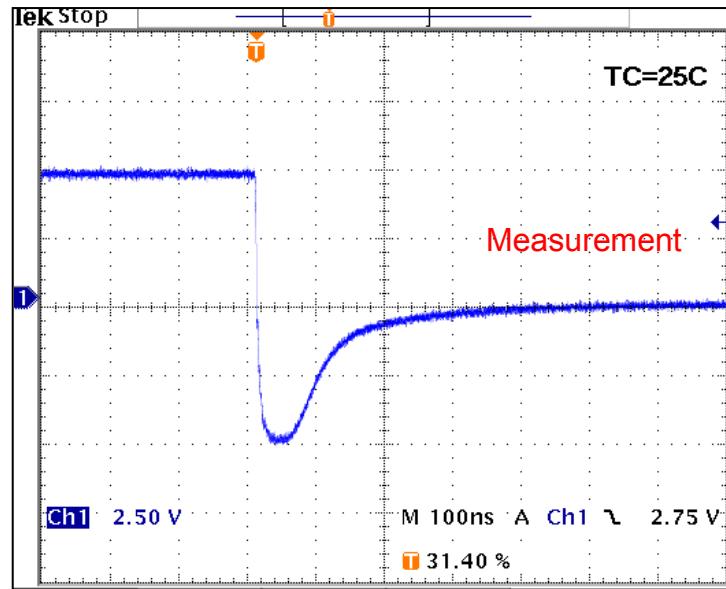


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trj	48.0	ns	47.7	ns	0.62
trb	134.0	ns	133.7	ns	0.22

Reverse Recovery Characteristic

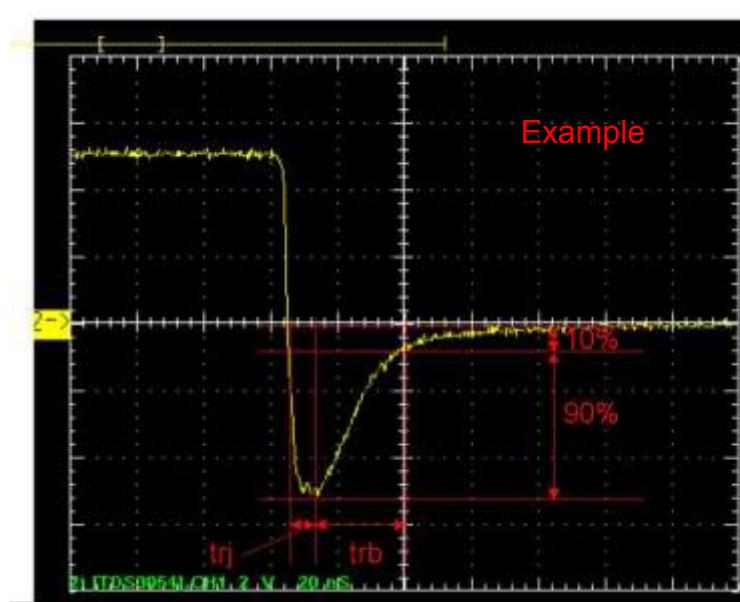
Reference



$Trj = 48(\text{ns})$

$Trb = 134(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.2(\text{A})$, $RI = 50$



Relation between trj and trb